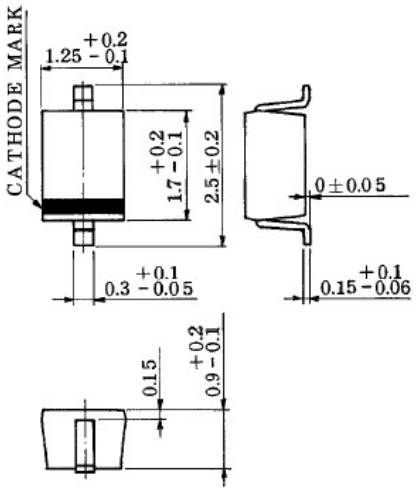
1SV229

VARIABLE CAPACITANCE DIODE SILICON EPITAXIAL PLANAR TYPE

VCO FOR UHF BAND RADIO

$r_s = 0.2\Omega$ (Typ.)



Weight : 0.004g

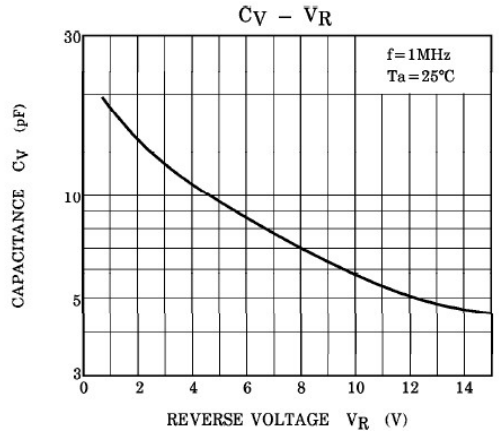
Unit in mm

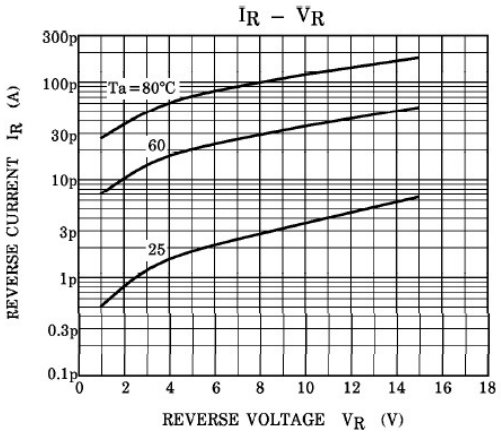
MAXIMUM RATINGS (Ta = 25°C)

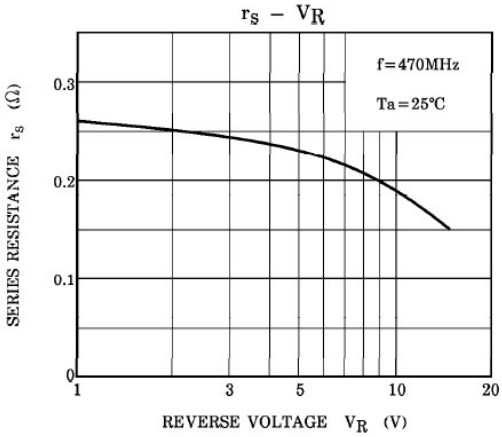
CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	15	V
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

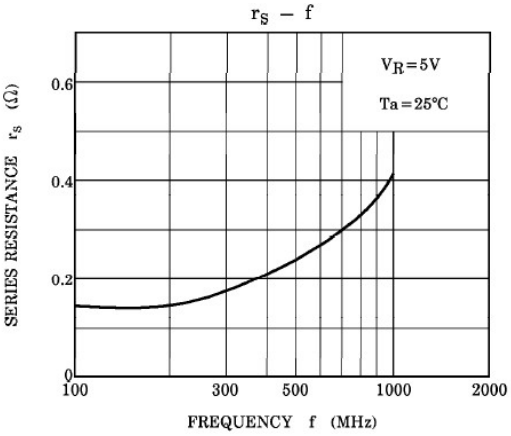
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

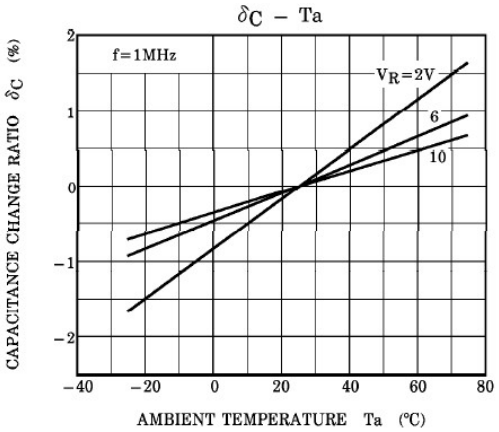
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	$I_R = 1\mu A$	15	—	—	V
Reverse Current	I_R	$V_R = 15V$	—	—	5	nA
Capacitance	C_{2V}	$V_R = 2V$, f = 1MHz	14	15	16	pF
Capacitance	C_{10V}	$V_R = 10V$, f = 1MHz	5.5	6	6.5	pF
Capacitance Ratio	C_{2V}/C_{10V}	—	2.0	2.5	—	—
Series Resistance	r_s	$V_R = 5V$, f = 470MHz	—	0.2	0.4	Ω











NOTE : $\delta_C\,(\%) = \dfrac{C\,(Ta) - C\,(25°C)}{C\,(25°C)} \times 100$